MOSFETs Silicon N-Channel MOS (U-MOSVII)

TPCC8093

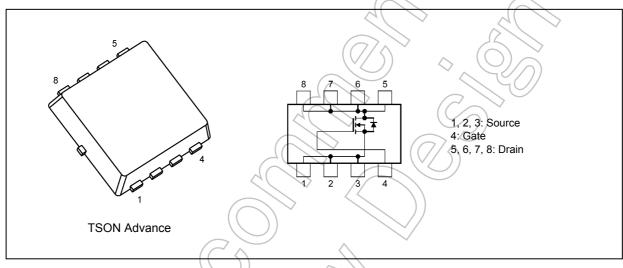
1. Applications

Lithium-Ion Secondary Batteries

2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 4.5 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 4.5 \text{ V})$
- (3) Low leakage current: I_{DSS} = 10 μ A (max) (V_{DS} = 20 V)
- (4) Enhancement mode: V_{th} = 0.5 to 1.2 V (V_{DS} = 10 V, I_{D} = 0.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics) (77^	Symbol	Rating	Unit
Drain-source voltage		$\langle \rangle \rangle$	V _{DSS}	20	V
Gate-source voltage			V _{GSS}	±12	1
Drain current (DC)	$\langle - \rangle$	(Note 1)	Ι _D	21	A
Drain current (pulsed)		(Note 1)	I _{DP}	63	
Power dissipation	(T _c = 25°C)		PD	30	W
Power dissipation	(t = 10 s)	(Note 2)	PD	1.9	W
Power dissipation	(t = 10 s)	(Note 3)	PD	0.7	W
Single-pulse avalanche energy	\bigcirc	(Note 4)	E _{AS}	81	mJ
Avalanche current			I _{AR}	21	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

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5. Thermal Characteristics

Characteris	tics		Symbol	Max	Unit
Channel-to-case thermal resistance	(T _c = 25°C)		R _{th(ch-c)}	4.16	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 2)	R _{th(ch-a)}	65.7	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	178	°C/W
Note 2: Device mounted on a glass-epoxy boat Note 3: Device mounted on a glass-epoxy boat Note 4: V_{DD} = 16 V, T_{ch} = 25°C (initial), L = 0.1 FR-4 25.4 × 25.4 × 0.1 (Unit: mm	rd (b), Figure 5.2 41 mH, R _G = 1 Ω, I _{AI} 8	R = 21 A	25.4 ×	FR-4 25.4 × 0.8 (Unit: mm)	
Fig. 5.1 Device Mounted on a Glass- Board (a)			ounted on a oard (b)	Glass-Ep	юху
Note: This transistor is sensitive to electrosta	tic discharge and sh	ould be handled	with care.		

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$	_		±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	$\langle \cdot \rangle$	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	20		_	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -12 V	8	$\langle \gamma \rangle$	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.5 mA	0.5	2_	1.2	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 2.5 V, I _D = 10.5 A	$/\uparrow$	6.8	9.5	mΩ
		V _{GS} = 4.5 V, I _D = 10.5 A	Y	4.5	5.8	

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	- /	1860	-	pF
Reverse transfer capacitance	C _{rss}		((140	_	
Output capacitance	C _{oss}		R	365) —	
Switching time (rise time)	tr	See Figure 6.2.1.	\sim	A	_	ns
Switching time (turn-on time)	t _{on}			11	—	
Switching time (fall time)	t _f		~_]	12	—	
Switching time (turn-off time)	t _{off}		\sim –	44	_	

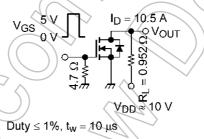


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

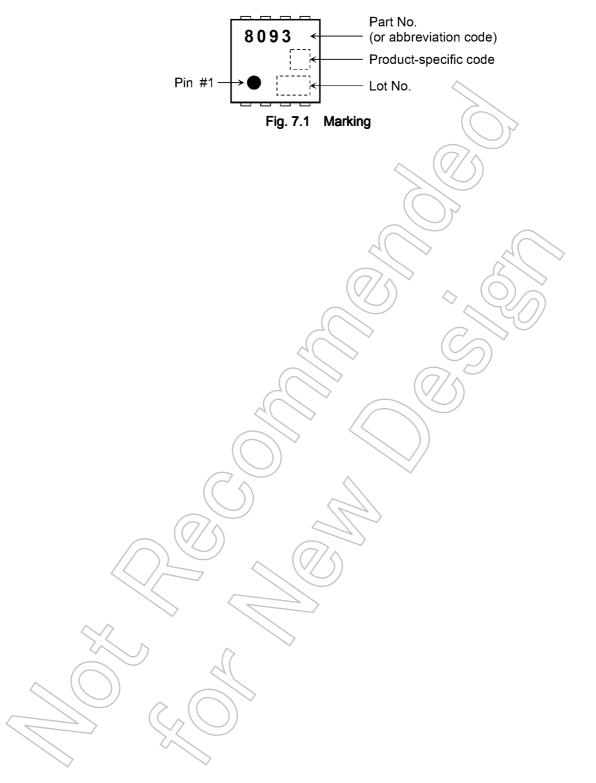
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q _g	V _{DD} ≈ 16 V, V _{GS} = 5 V, I _D = 21 A	_	16	—	nC
Gate-source charge 1	Q _{gs1}		_	4	—	
Gate-drain charge	Qgd			3.1	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

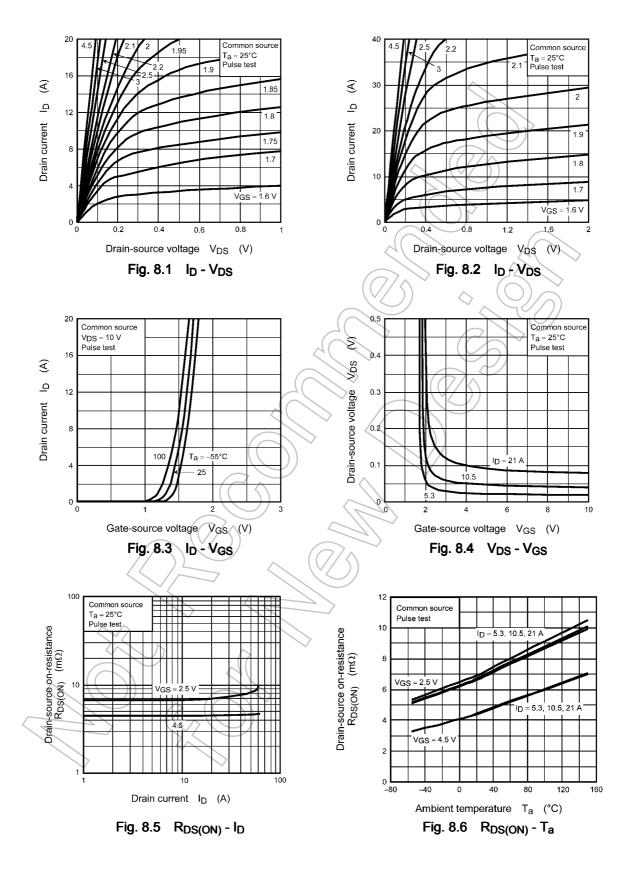
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 5)	I _{DRP}	—	_	_	63	А
Diode forward voltage	V _{DSF}	I _{DR} = 21 A, V _{GS} = 0 V			-1.2	V

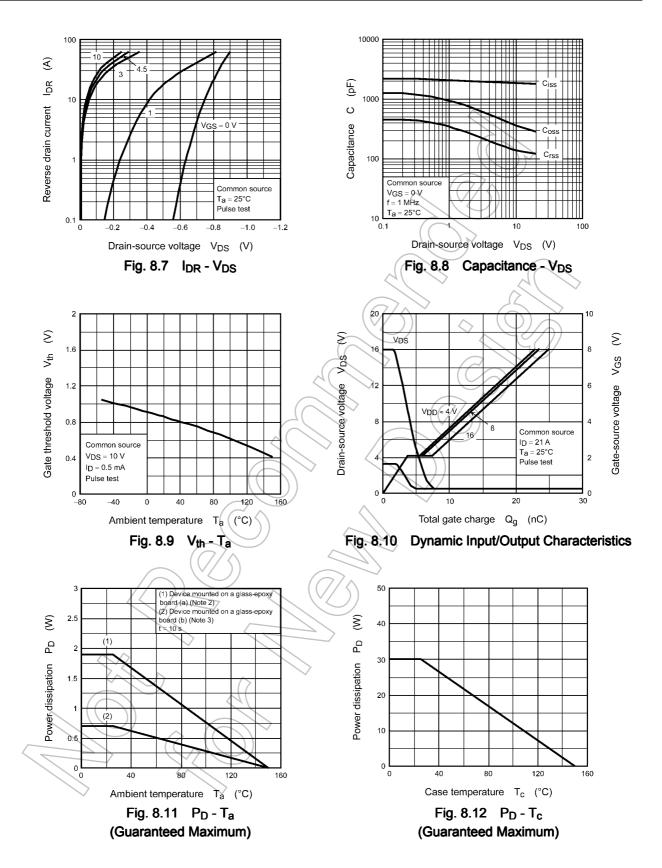
Note 5: Ensure that the channel temperature does not exceed 150°C.

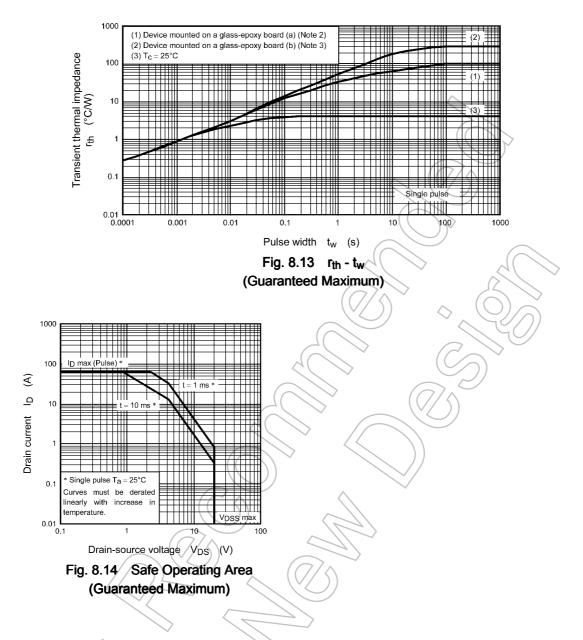
7. Marking



8. Characteristics Curves (Note)







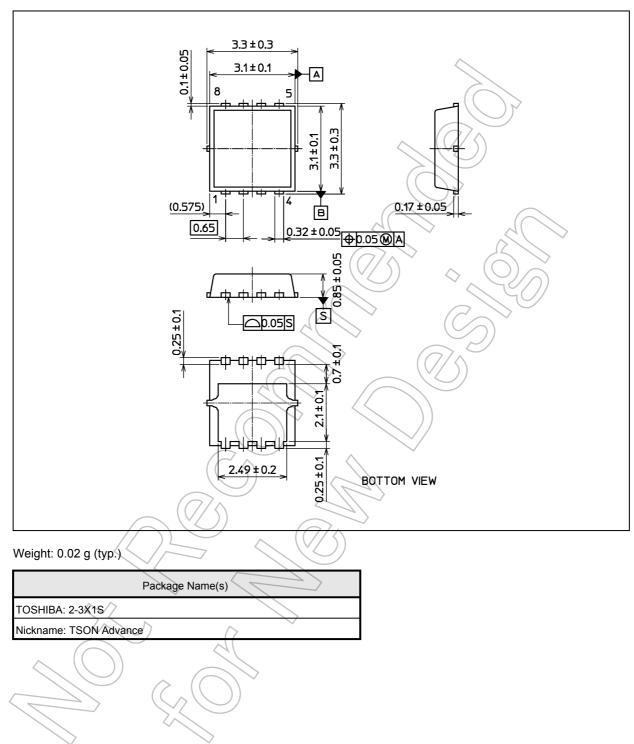
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

TPCC8093

Unit: mm



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